

MCR8SD, MCR8SM, MCR8SN

Preferred Device

Sensitive Gate Silicon Controlled Rectifiers Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

Features

- Sensitive Gate Allows Triggering by Microcontrollers and other Logic Circuits
- Blocking Voltage to 800 V
- On-State Current Rating of 8 A RMS at 80°C
- High Surge Current Capability – 80 A
- Rugged, Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dv/dt – 5 V/ μ sec Minimum at 110°C
- Pb-Free Packages are Available*

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) ($T_J = -40$ to 110°C , Sine Wave, 50 to 60 Hz)	V_{DRM} , V_{RRM}	400 600 800	V
On-State RMS Current (180° Conduction Angles; $T_C = 80^\circ\text{C}$)	$I_{T(RMS)}$	8.0	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = 110^\circ\text{C}$)	I_{TSM}	80	A
Circuit Fusing Consideration ($t = 8.33$ ms)	I^2t	26.5	A^2sec
Forward Peak Gate Power (Pulse Width ≤ 10 μ s, $T_C = 80^\circ\text{C}$)	P_{GM}	5.0	W
Forward Average Gate Power ($t = 8.3$ ms, $T_C = 80^\circ\text{C}$)	$P_{G(AV)}$	0.5	W
Forward Peak Gate Current (Pulse Width ≤ 10 μ s, $T_C = 80^\circ\text{C}$)	I_{GM}	2.0	A
Operating Junction Temperature Range	T_J	-40 to 110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to 150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

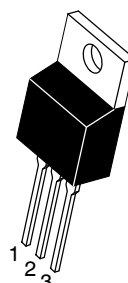
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

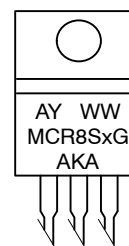
<http://onsemi.com>

SCRs
8 AMPERES RMS
400 thru 800 VOLTS



TO-220AB
CASE 221A-09
STYLE 3

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
x = D, M, or N
G = Pb-Free Package
AKA = Diode Polarity

PIN ASSIGNMENT

Pin	Assignment
1	Cathode
2	Anode
3	Gate
4	Anode

ORDERING INFORMATION

Device	Package	Shipping
MCR8SD	TO-220AB	50 Units / Rail
MCR8SDG	TO-220AB (Pb-Free)	50 Units / Rail
MCR8SM	TO-220AB	50 Units / Rail
MCR8SMG	TO-220AB (Pb-Free)	50 Units / Rail
MCR8SN	TO-220AB	50 Units / Rail
MCR8SNG	TO-220AB (Pb-Free)	50 Units / Rail

Preferred devices are recommended choices for future use and best overall value.

MCR8SD, MCR8SM, MCR8SN

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.2	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient	$R_{\theta JA}$	62.5	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current (Note 3) ($V_D = \text{Rated } V_{DRM} \text{ and } V_{RRM}; R_{GK} = 1 \text{ k}\Omega$)	I_{DRM}, I_{RRM}	–	–	10	μA
$T_J = 25^{\circ}\text{C}$ $T_J = 110^{\circ}\text{C}$		–	–	500	

ON CHARACTERISTICS

Peak Forward On-State Voltage (Note 2) ($I_{TM} = 16 \text{ A}$)	V_{TM}	–	–	1.8	V
Gate Trigger Current (Continuous dc) (Note 4) ($V_D = 12 \text{ V}; R_L = 100 \Omega$)	I_{GT}	5.0	25	200	μA
Holding Current (Note 3) ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = 200 mA)	I_H	–	0.5	6.0	mA
Latch Current (Note 4) ($V_D = 12 \text{ V}, I_G = 200 \mu\text{A}$)	I_L	–	0.6	8.0	mA
Gate Trigger Voltage (Continuous dc) (Note 4) ($V_D = 12 \text{ V}; R_L = 100 \Omega$)	V_{GT}	0.3	0.65	1.0	V
		–	–	1.5	
Gate Non-Trigger Voltage ($V_D = 12 \text{ V}, R_L = 100 \Omega$)	V_{GD}	0.2	–	–	V
$T_J = 25^{\circ}\text{C}$ $T_J = -40^{\circ}\text{C}$ $T_J = 110^{\circ}\text{C}$					

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage ($V_D = 67\% V_{DRM}, R_{GK} = 1 \text{ k}\Omega, C_{GK} = 0.1 \mu\text{F}, T_J = 110^{\circ}\text{C}$)	dv/dt	5.0	15	–	$\text{V}/\mu\text{s}$
Critical Rate of Rise of On-State Current IPK = 50 A, Pw = 40 μsec , $di/dt = 1 \text{ A}/\mu\text{sec}$, $I_{gt} = 10 \text{ mA}$	di/dt	–	–	100	$\text{A}/\mu\text{s}$

2. Indicates Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

3. $R_{GK} = 1000 \text{ Ohms}$ included in measurement.

4. Does not include R_{GK} in measurement.

MCR8SD, MCR8SM, MCR8SN

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current

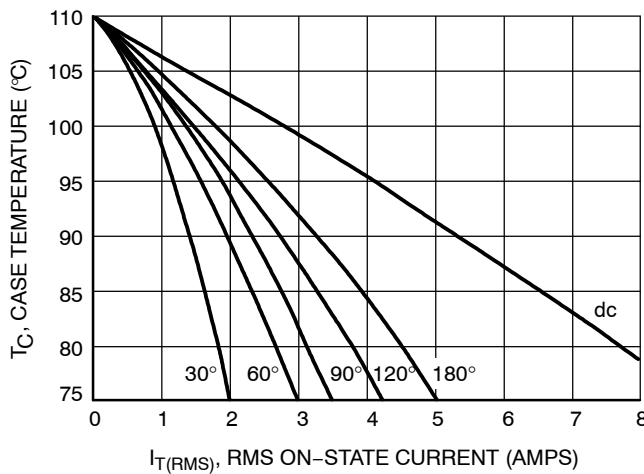
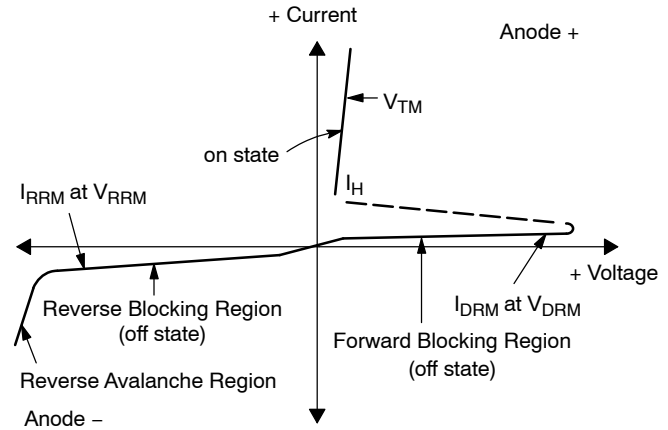


Figure 1. Typical RMS Current Derating

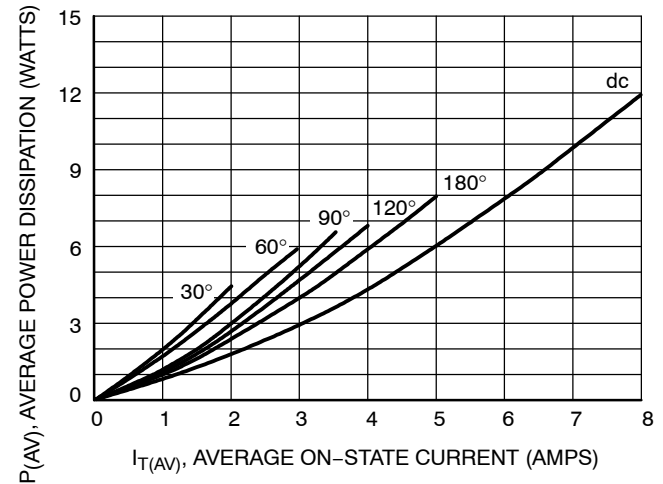


Figure 2. On-State Power Dissipation

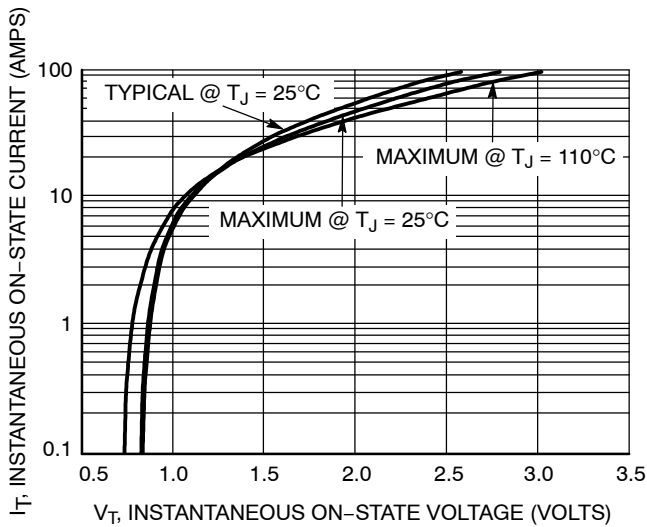


Figure 3. Typical On-State Characteristics

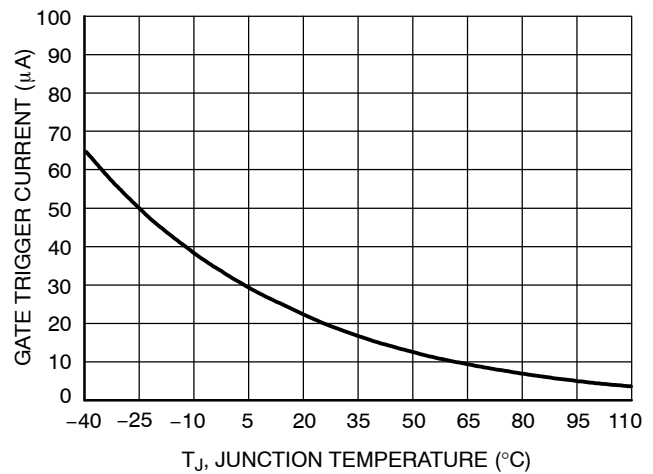


Figure 4. Typical Gate Trigger Current versus Junction Temperature

MCR8SD, MCR8SM, MCR8SN

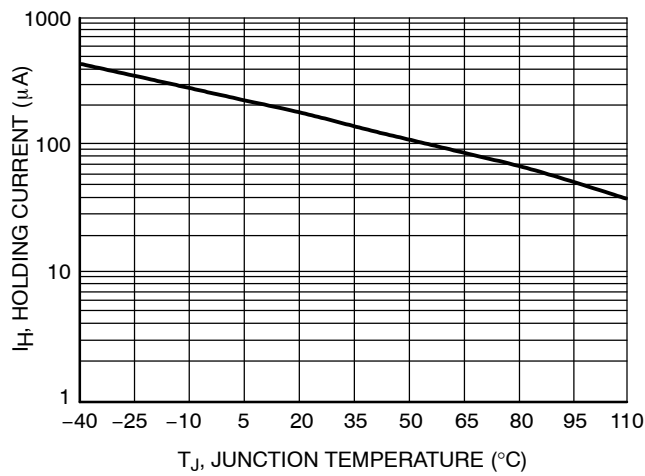


Figure 5. Typical Holding Current versus Junction Temperature

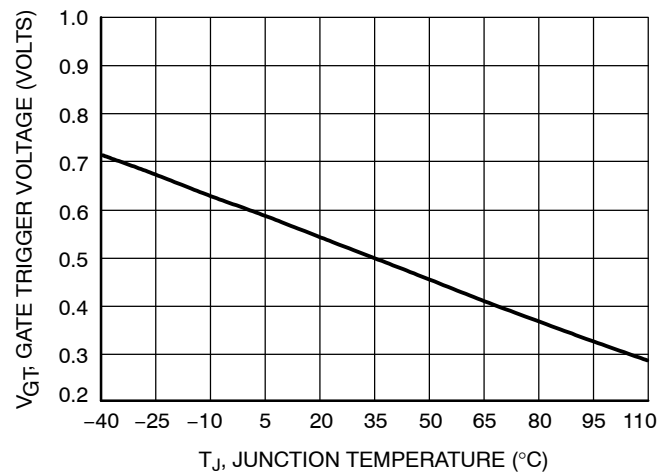


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

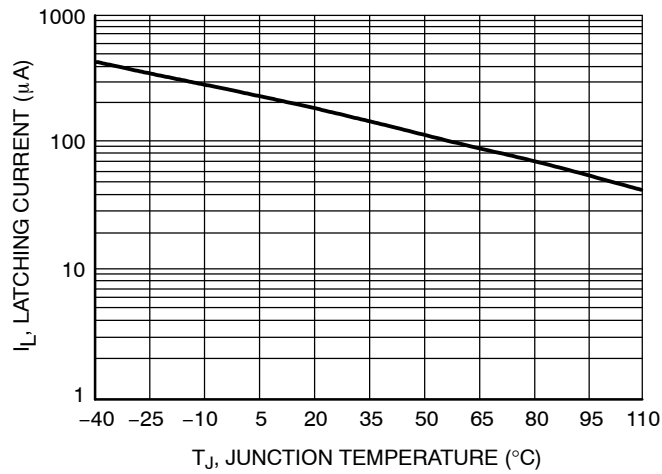
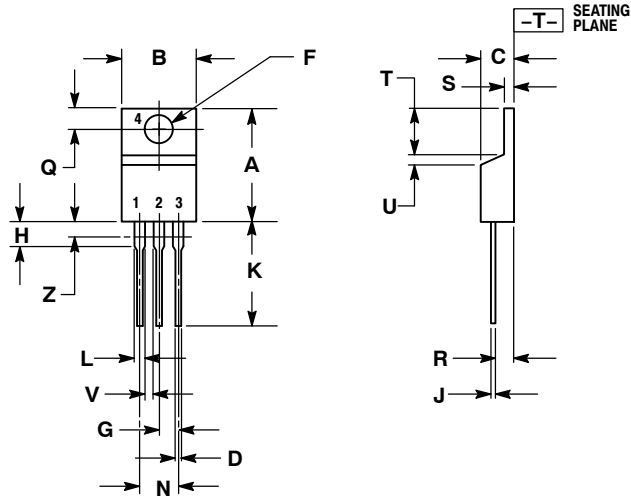


Figure 7. Typical Latching Current versus Junction Temperature

MCR8SD, MCR8SM, MCR8SN

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AF



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 3:
- PIN 1. CATHODE
 - ANODE
 - GATE
 - ANODE

ON Semiconductor and **ON** are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.